## **Switch-mode Power Rectifiers**

These state-of-the-art devices are a series designed for use in switching power supplies, inverters and as free wheeling diodes.

#### **Features**

- Ultrafast 35 and 60 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- High Voltage Capability to 600 V
- ESD Ratings:
  - ◆ Machine Model = C
  - ♦ Human Body Model = 3B
- Low Forward Drop
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating Specified @ Both Case and Ambient Temperatures
- SUR8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- All Packages are Pb-Free\*

#### **Mechanical Characteristics:**

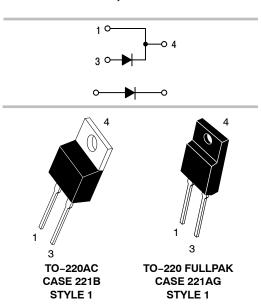
- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



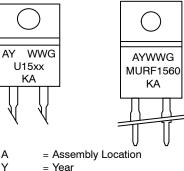
## ON Semiconductor®

http://onsemi.com

## **ULTRAFAST RECTIFIERS** 15 AMPERES, 100-600 VOLTS



## MARKING DIAGRAMS



WW = Work Week = Pb-Free Package U15xx = Device Code

xx = 10, 15, 20, 40 or 60

= Diode Polarity

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **MAXIMUM RATINGS**

		MUR/SUR8					
Rating	Symbol	1510	1515	1520	1540	1560	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	150	200	400	600	V
Average Rectified Forward Current (Rated V <sub>R</sub> )	I <sub>F(AV)</sub>	15 @ T <sub>C</sub> = 150°C		Α			
Peak Rectified Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz)	I <sub>FRM</sub>	30 @ T <sub>C</sub> = 150°C		30 @ T <sub>C</sub> = 145°C	Α		
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I <sub>FSM</sub>	200 150		150	Α		
Operating Junction Temperature and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +175		°C			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
MUR1510 Series: Thermal Resistance Junction-to-Case Junction-to-Ambient	$egin{array}{c} R_{ heta JC} \ R_{ heta JA} \end{array}$	1.5 73	°C/W
MURF1560: Thermal Resistance Junction-to-Case Junction-to-Ambient	R <sub>θJC</sub> R <sub>θJA</sub>	4.25 75	°C/W

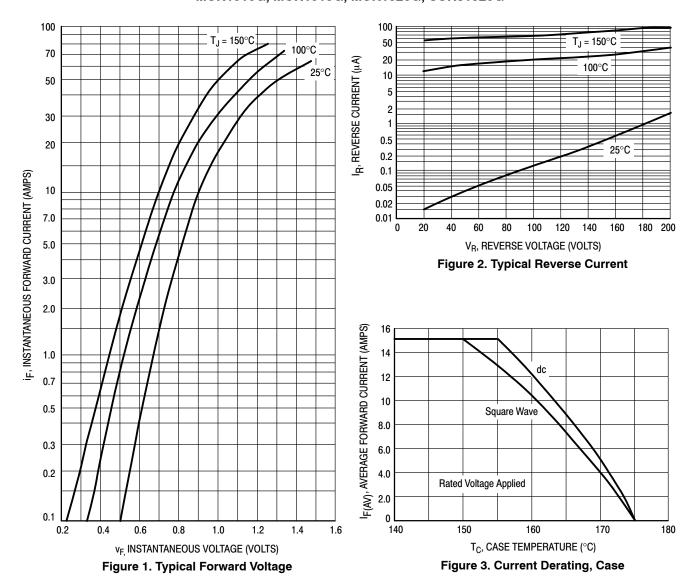
### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	1510	1515	1520	1540	1560	Unit
Maximum Instantaneous Forward Voltage (Note 1) (i <sub>F</sub> = 15 A, T <sub>C</sub> = 150°C) (i <sub>F</sub> = 15 A, T <sub>C</sub> = 25°C)	VF		0.85 1.05		1.12 1.25	1.20 1.50	V
Maximum Instantaneous Reverse Current (Note 1) (Rated DC Voltage, T <sub>C</sub> = 150°C) (Rated DC Voltage, T <sub>C</sub> = 25°C)	iR		500 10		500 10	1000 10	μΑ
Maximum Reverse Recovery Time (I <sub>F</sub> = 1.0 A, di/dt = 50 A/μs)	t <sub>rr</sub>		35			60	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2.0%.

## MUR1510G, MUR1515G, MUR1520G, SUR81520G



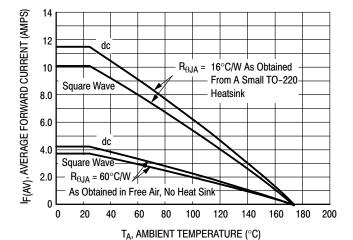


Figure 4. Current Derating, Ambient

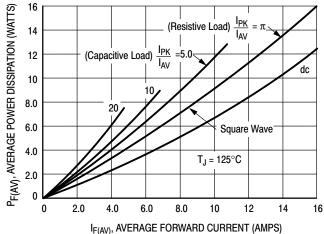
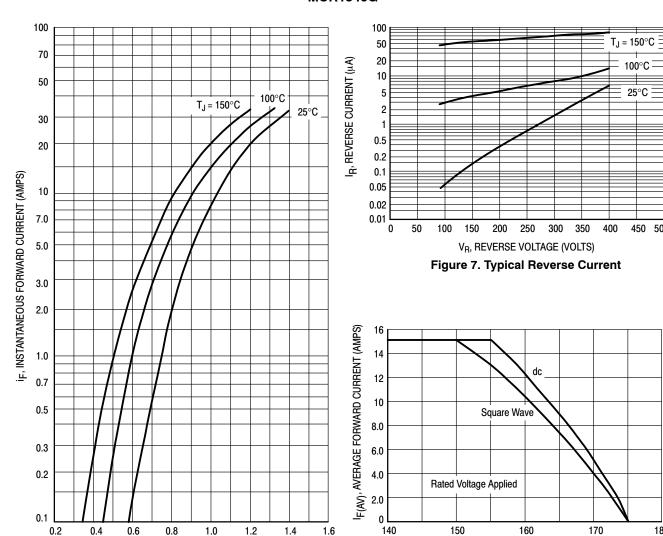


Figure 5. Power Dissipation

## MUR1540G



**VF INSTANTANEOUS VOLTAGE (VOLTS)** Figure 6. Typical Forward Voltage

T<sub>C</sub>, CASE TEMPERATURE (°C) Figure 8. Current Derating, Case

180

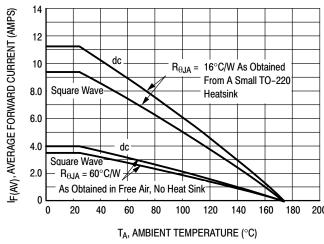


Figure 9. Current Derating, Ambient

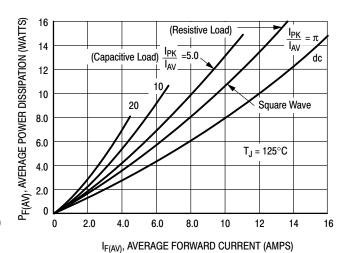


Figure 10. Power Dissipation

## MUR1560G, MURF1560G, SUR81560G

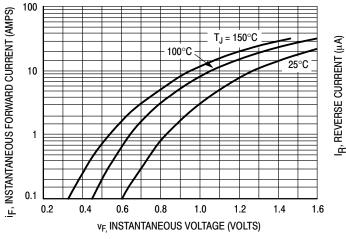
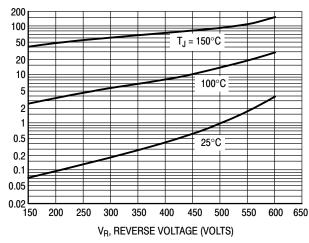


Figure 11. Typical Forward Voltage



**Figure 12. Typical Reverse Current** 

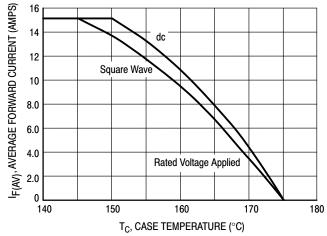


Figure 13. Current Derating, Case

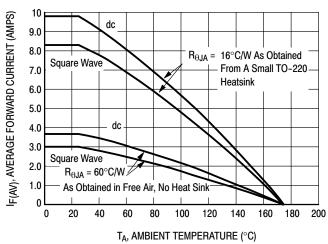


Figure 14. Current Derating, Ambient

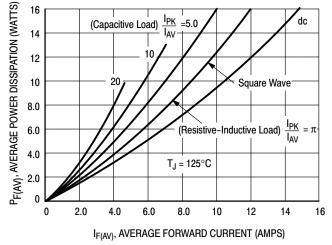


Figure 15. Power Dissipation

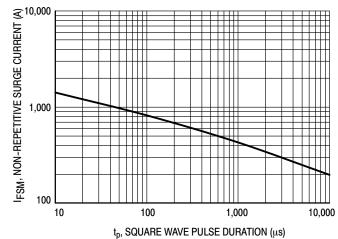


Figure 16. Typical Non-Repetitive Surge Current

<sup>\*</sup> Typical performance based on a limited sample size. ON Semiconductor does not guarantee ratings not listed in the Maximum Ratings table.

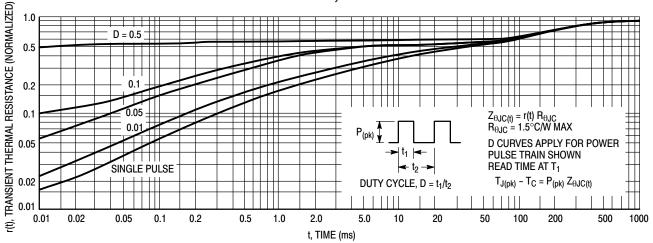


Figure 17. Thermal Response

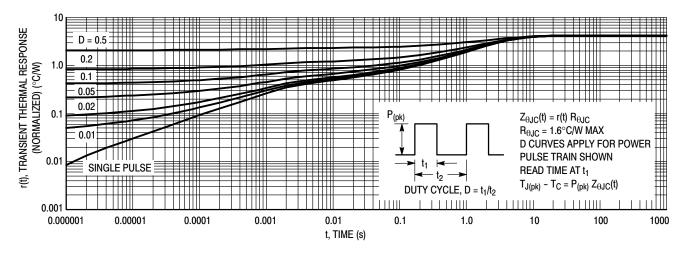


Figure 18. Thermal Response, (MURF1560G) Junction-to-Case (R<sub>B,IC</sub>)

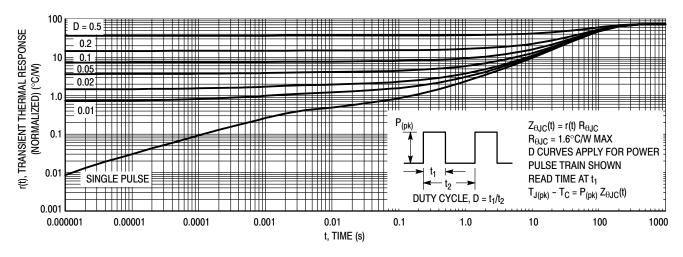


Figure 19. Thermal Response, (MURF1560G) Junction–to–Ambient ( $R_{\theta JA}$ )

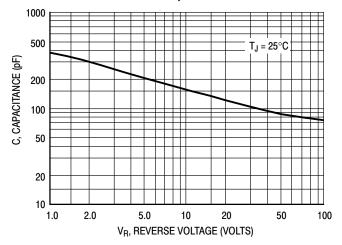
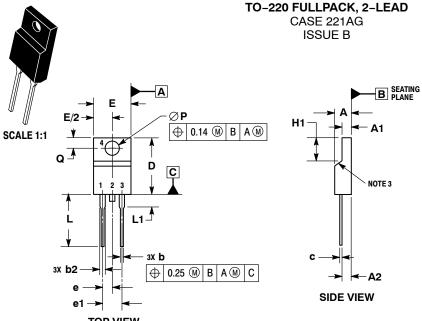


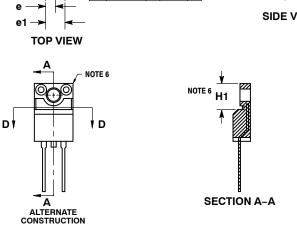
Figure 20. Typical Capacitance

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MUR1510G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1515G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1520G	TO-220AC (Pb-Free)	50 Units / Rail
SUR81520G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1540G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1560G	TO-220AC (Pb-Free)	50 Units / Rail
SUR81560G	TO-220AC (Pb-Free)	50 Units / Rail
MURF1560G	TO-220FP (Pb-Free)	50 Units / Rail

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





**DATE 27 AUG 2015** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

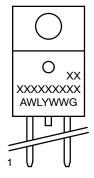
  3. CONTOUR UNCONTROLLED IN THIS AREA.

  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS AND TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.

  5. DIMENSION DE DOES NOT INCLUDE DAMBAR
- PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

	MILLIMETERS				
DIM	MIN MAX				
Α	4.30	4.70			
A1	2.50	2.90			
A2	2.50	2.90			
b	0.54	0.84			
b2	1.10	1.40			
С	0.49	0.79			
D	14.22	15.88			
Ε	9.65	10.67			
е	2.54	BSC			
e1	5.08 BSC				
H1	6.40	6.90			
L	12.70	14.73			
L1		2.80			
P	3.00	3.40			
Q	2.80	3.20			

## **GENERIC MARKING DIAGRAM\***



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

= Pb-Free Package G

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	TO-220 FULLPACK, 2-LE	AD	PAGE 1 OF 1

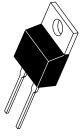
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SECTION D-D

## **MECHANICAL CASE OUTLINE**

**PACKAGE DIMENSIONS** 





SCALE 1:1

TO-220, 2-LEAD CASE 221B-04 ISSUE F

**DATE 12 APR 2013** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

Q

STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE

PIN 1. ANODE 2. N/A 3. CATHODE 4. ANODE

DECODIDEION	TO-220, 2-LEAD		PAGE 1 OF 1
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